

# **UNIVERSITI PUTRA MALAYSIA**

CHARACTERIZATION AND DIELECTRIC PROPERTIES OF PURE AND Er-SUBSTITUTED Bi4Ti3O12 AND Bi5CrTi3O15 AURIVILLIUS CERAMICS

WONG YICK JENG

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## CHARACTERIZATION AND DIELECTRIC PROPERTIES OF PURE AND Er-SUBSTITUTED Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> AND Bi<sub>5</sub>CrTi<sub>3</sub>O<sub>15</sub> AURIVILLIUS CERAMICS



Thesis Submitted to the School of Graduate Studies, Universiti Putra Malaysia, in Fulfilment of the Requirements for the Degree of Doctor of Philosophy

January 2018

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Abstract of thesis presented to the Senate of Universiti Putra Malaysia in fulfilment of the requirement for the degree of Doctor of Philosophy

## CHARACTERIZATION AND DIELECTRIC PROPERTIES OF PURE AND Er-SUBSTITUTED Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> AND Bi<sub>5</sub>CrTi<sub>3</sub>O<sub>15</sub> AURIVILLIUS CERAMICS

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January 2018

### Chair: Jumiah binti Hassan, PhD Faculty: Institute of Advanced Technology

Aurivillius compounds,  $(Bi_2O_2)^{2+}(Bi_{n-1}Ti_nO_{3n+1})^{2-}$ , are structurally constructed by alternately stacking n perovskite units of  $(Bi_{n-1}Ti_nO_{3n+1})^{2-}$  with two fluorite-like layers of  $(Bi_2O_2)^{2+}$ . Three-layered  $Bi_4Ti_3O_{12}$  system in this kind of compounds is extensively studied. In most cases, the modification is done by doping various types of rare-earth ions at Bi-site to reduce high electrical conductivity for more effective ferroelectric dielectrics. Unlike the three-layered Aurivillius systems, attention to the four-layered Aurivillius systems isostructural with  $Bi_5FeTi_3O_{15}$  is scarce, especially  $Bi_5CrTi_3O_{15}$ . Such a case involving the magnetic  $Cr^{3+}$  ions was only reported from the analysis of powder neutron diffraction data.

Preparation of the Aurivillius compounds is commonly done by conventional solid state reaction method. However, this economical method requires high-temperature solid state reaction to reach single phase. Here, high energy milling at room temperature for the mechanosynthesis of Aurivillius compounds with  $Bi_4Ti_3O_{12}$ ,  $Bi_{3.25}Er_{0.75}Ti_3O_{12}$ ,  $Bi_5CrTi_3O_{15}$ , and  $Bi_{4.25}Er_{0.75}CrTi_3O_{15}$  compositions is employed. These mechanosynthesized samples subjected to a range of sintering temperatures (700 – 1000°C) are systematically compared with the conventionally processed samples in terms of X-ray Diffraction (XRD) analysis, Field Emission Scanning Electron Microscopy (FE-SEM) observation, dielectric, and density measurements.

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All the comparative results obtained point to the effectiveness of the high energy milling over the conventional processing technique as a more efficient solid-phase formation method in synthesizing the studied samples. This is first demonstrated by room-temperature XRD studies. The sintering temperature at which these mechanosynthesized compounds show complete formation of the pure phase are comparatively lower than those of conventionally processed samples as a result of the mechanochemical reaction by high energy milling.

Consequently, FE-SEM observations of the mechanosynthesized samples reveal distinct grain morphologies contrary to the plate-like grain morphologies in the conventionally processed samples, in which the latter display grain growth with increasing sintering temperature controlled by anisotropic grain boundary. For the mechanosynthesized  $Bi_4Ti_3O_{12}$ , triple junction controlled grain growth is evident, while the grain growth of mechanosynthesized  $Bi_{4.25}Er_{0.75}CrTi_3O_{15}$  is discovered for the first time being governed via multiple ordered coalescence of nanocrystals. Also, the mechanosynthesized samples. For this reason, the mechanosynthesized samples exhibit much higher room-temperature dielectric constant values in the frequency range of 100 Hz – 10 MHz.

All samples prepared by both methods exhibit common feature in the variation of dielectric constant with respect to frequency, which follows directly from the relationship between densification and sintering temperature. Moreover, very similar intrinsic frequency dispersion of dielectric responses could be observed, with the physical basis for the interpretation is based on the empirical fitting model of relaxation functions: Cole-Cole, Cole-Davidson, and Havriliak-Negami.

Besides comparison of methods, the influence of  $Er^{3+}$  dopant on the parent structure of Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> and Bi<sub>5</sub>CrTi<sub>3</sub>O<sub>15</sub> is also investigated. The marked contributions of this dopant are from the grain growth inhibition due to the grain boundary segregation of  $Er^{3+}$  and weak low-frequency dispersion of the dielectric constant in the doped samples. These experimental evidences reflect the suppression of oxygen vacancies, which is also manifested in one of the fitting parameters, the reduced direct current conductivity. Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia sebagai memenuhi keperluan untuk ijazah Doktor Falsafah

## PENCIRIAN DAN SIFAT DIELEKTRIK SERAMIK AURIVILLIUS Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> DAN Bi<sub>5</sub>CrTi<sub>3</sub>O<sub>15</sub> DALAM BENTUK TULEN DAN Er-TERTUKAR GANTI

Oleh

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Penstrukturan sebatian Aurivillius,  $(Bi_2O_2)^{2+}(Bi_{n-1}Ti_nO_{3n+1})^{2-}$ , adalah secara susunan selang n unit perovskit  $(Bi_{n-1}Ti_nO_{3n+1})^{2-}$  dengan dua lapisan bak fluorit  $(Bi_2O_2)^{2+}$ . Sistem  $Bi_4Ti_3O_{12}$  berlapis tiga dalam sebatian jenis ini telah dikaji dengan meluas. Dalam kebanyakan kes, ia diubah suai menerusi pendopan dengan pelbagai ion nadir bumi di tapak-Bi untuk mengurangkan kekonduksian elektrik demi feroelektrik dielektrik yang lebih berkesan. Tidak serupa dengan sistem Aurivillius berlapis tiga, perhatian kepada sistem Aurivillius berlapis empat yang isostruktur dengan  $Bi_5FeTi_3O_{15}$  adalah kurang, terutamanya  $Bi_5CrTi_3O_{15}$ . Kes seperti ini yang melibatkan ion magnet  $Cr^{3+}$  hanya dilaporkan dari analisis data pembelauan neutron serbuk.

Penyediaan sebatian Aurivillius biasanya dilakukan dengan menggunakan kaedah tindak balas keadaan pepejal konvensional. Namun begitu, kaedah berekonomi ini memerlukan tindak balas keadaan pepejal yang bersuhu tinggi untuk mencapai fasa tunggal. Di sini, kisaran bertenaga tinggi pada suhu bilik digunakan untuk sintesis mekanik sebatian Aurivillius dengan komposisi Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>, Bi<sub>3.25</sub>Er<sub>0.75</sub>Ti<sub>3</sub>O<sub>12</sub>, Bi<sub>5</sub>CrTi<sub>3</sub>O<sub>15</sub>, dan Bi<sub>4.25</sub>Er<sub>0.75</sub>CrTi<sub>3</sub>O<sub>15</sub>. Perbandingan sistematik bagi sampel-sampel tersintesis secara mekanik ini yang disinter pada julat suhu di antara 700 – 1000°C dengan sampel-sampel terproses scara konventional adalah dari segi analisis belauan sinar-X (XRD), cerapan mikroskopi elektron pengimbasan pancaran medan (FE-SEM), pengukuran dielektrik, dan ketumpatan.

Kesemua keputusan perbandingan yang diperoleh menghala tuju kepada keberkesanan kisaran bertenaga tinggi sebagai kaedah pembentukan fasa pepejal yang lebih cekap daripada teknik pemprosesan konvensional dalam mensintesiskan sampel kajian. Demonstrasi pertama ini adalah dari kajian XRD pada suhu bilik. Suhu pensinteran di mana sampel-sampel tersintesis secara mekanik ini



menunjukkan pembentukan lengkap fasa tulen adalah lebih rendah berbanding dengan sampel-sampel terproses scara konvensional akibat tindak balas kimia mekanik menerusi kisaran bertenaga tinggi.

Oleh sebab itu, permerhatian FE-SEM bagi sampel-sampel tersintesis secara mekanik mendedahkan morfologi butiran berbeza yang berlawanan dengan morfologi bak plat pada sampel-sampel terproses scara konventional, di mana morfologi yang kedua memaparkan pertumbuhan butiran dengan peningkatan suhu pensinteran yang dikawal secara sempadan butiran anisotropi. Bagi sampel  $Bi_4Ti_3O_{12}$  yang tersintesis secara mekanik, pertumbuhan butiran kawalan simpangan tiga adalah jelas, sedangkan pertumbuhan bijian  $Bi_{4.25}Er_{0.75}CrTi_3O_{15}$  dikawal melalui koalesens tertib berganda hablur nano merupakan penemuan yang pertama kali. Juga, kesan kimia mekanik mencetuskan penumpatan tersinter yang lebih baik dalam sampel. Atas sebab ini, sampel-sampel tersintesis secara mekanik menunjukkan nilai pemalar dielektrik yang lebih tinggi pada suhu bilik dalam julat frekuensi 100 Hz – 10 MHz.

Kesemua sampel yang disediakan oleh kedua-dua kaedah menunjukkan sifat sepunya dalam perubahan pemalar dielektrik merujuk kepada frekuensi, yang mana ianya mengikut secara langsung dari perhubungan antara penumpatan dan suhu pensinteran. Tambahan pula, serakan frekuensi intrinsik sambutan dielektrik yang sangat serupa dapat diperhatikan, dengan asas fizikal untuk pentafsiran adalah berdasarkan model penyuaian empirik fungsi kesantaian: Cole-Cole, Cole-Davidson, dan Havriliak-Negami.

Selain daripada kaedah bandingan, pengaruh dopan  $Er^{3+}$  terhadap struktur induk  $Bi_4Ti_3O_{12}$  dan  $Bi_5CrTi_3O_{15}$  turut disiasat. Sumbangan ketara dopan tersebut adalah dari perencatan pertumbuhan butiran disebabkan oleh pengasingan sempadan butiran  $Er^{3+}$  dan serakan frekuensi rendah pemalar dielektrik yang lemah dalam sampel-sampel terdop. Bukti-bukti eksperimen ini mencerminkan penindasan kekosongan oksigen, dinyatakan dalam salah satu parameter penyuaian juga, iaitu kekonduksian arus terus terkurang.

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I certify that a Thesis Examination Committee has met on 10 January 2018 to conduct the final examination of Wong Yick Jeng on his thesis entitled "Characterization and Dielectric Properties of Pure and Er-Substituted Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> and Bi<sub>5</sub>CrTi<sub>3</sub>O<sub>15</sub> Aurivillius Ceramics" in accordance with the Universities and University Colleges Act 1971 and the Constitution of the Universiti Putra Malaysia [P.U.(A) 106] 15 March 1998. The Committee recommends that the student be awarded the Doctor of Philosophy.

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- 4.60 Series-parallel Type of R-C Equivalent Circuit Used to Describe the Impedance Behaviours of BTO-CM (700 1000°C), BCTO-CM (700 850°C), BTO-HM (700 1000°C), BTO:Er<sup>3+</sup>-HM (700 1000°C), BCTO-HM (700 850°C), and BCTO:Er<sup>3+</sup>-HM (700 850°C). Indices: el= Electrode, gb= Grain Boundary, g= Grain, R= Resistance, C= Capacitance, CPE= Constant Phase Element
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4.67 Nyquist Plot of BCTO-CM Sintered at (a) 900°C, (b) 950°C, and (c) 1000°C. Open Symbols are the Experimental Data Points, All are Fitted with the Solid Lines According to the Equivalent Circuit Model Given in (d). Arrows Indicate the Direction of Increasing Frequency

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- 4.72 Comparison of Log-log  $\varepsilon_{r}(\omega)$  between (a) BTO-CM and BTO-HM, (b) BTO: $Er^{3+}$ -CM and BTO: $Er^{3+}$ -HM, (c) BCTO-CM and BCTO-HM, (d) BCTO: $Er^{3+}$ -CM and BCTO: $Er^{3+}$ -HM at Some Selected Sintering Temperatures

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Logarithmic Frequency Dependence of  $\varepsilon_r$  and  $\varepsilon_r$ Measured over a Range of Elevated Temperatures in the Sample of BTO-CM Sintered at (a) 950°C and (b) 1000°C. Open Symbols are the Experimental Data, and Solid Line Approximations to the Observed Responses are in Accordance with Equation (4.1). Arrows Indicate the Direction of Increasing Measured Temperature

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# LIST OF ABBREVIATIONS

PZT	Lead zirconium titanate
Fe-RAMs	Ferroelectric random access memories
DRAMs	Dynamic random access memories
FE-PE	Ferroelectric-paraelectric phase transition
SHS	Self-propagating high-temperature synthesis
FTIR	Fourier transform infrared spectroscopy
TGA	Thermogravimetric analysis
DTA	Differential thermal analysis
XRD	X-ray diffraction
XPS	X-ray photoelectron spectroscopy
SEM	Scanning electron microscopy
TEM	Transmission electron microscopy
EDS	Energy dispersive X-ray spectroscopy
EXAFS	Extended X-ray absorption fine structure
BPR	Ball-to-powder weight ratio
MCA	Mechanochemical activation
SSR	Solid-state reaction
Log	Logarithm
CPE	Constant phase element
ICSD	Inorganic crystal structure database
FWHM	Breath of the peak at half of maximum intensity
CC	Cole-Cole
CD	Cole-Davidson
HN	Havriliak-Negami
IBLC	Internal barrier layer capacitor
SBLC	Surface barrier layer capacitor
MUT	Material under test
ESRF	European synchrotron radiation facility
LFD	Low-frequency dispersion
BTO-CM	Heat-treated Bi <sub>2</sub> O <sub>3</sub> -TiO <sub>2</sub> after conventional milling
BTO:Er <sup>3+</sup> -CM	Heat-treated Bi <sub>2</sub> O <sub>3</sub> -Er <sub>2</sub> O <sub>3</sub> -TiO <sub>2</sub> after conventional milling
BCTO-CM	Heat-treated Bi <sub>2</sub> O <sub>3</sub> -Cr <sub>2</sub> O <sub>3</sub> -TiO <sub>2</sub> after conventional milling
BCTO:Er <sup>3+</sup> -	Heat-treated Bi <sub>2</sub> O <sub>3</sub> -Er <sub>2</sub> O <sub>3</sub> -Cr <sub>2</sub> O <sub>3</sub> -TiO <sub>2</sub> after conventional
СМ	milling
BTO-HM	Heat-treated Bi <sub>2</sub> O <sub>3</sub> -TiO <sub>2</sub> after high energy milling
BTO:Er <sup>3+</sup> -HM	Heat-treated Bi <sub>2</sub> O <sub>3</sub> -Er <sub>2</sub> O <sub>3</sub> - TiO <sub>2</sub> after high energy milling
BCTO-HM	Heat-treated Bi <sub>2</sub> O <sub>3</sub> - Cr <sub>2</sub> O <sub>3</sub> -TiO <sub>2</sub> after high energy milling
BCTO:Er <sup>3+</sup> -	Heat-treated Bi <sub>2</sub> O <sub>3</sub> -Er <sub>2</sub> O <sub>3</sub> -Cr <sub>2</sub> O <sub>3</sub> -TiO <sub>2</sub> after high energy
HM	milling

## LIST OF SYMBOLS

n	Number of oxygen octahedra in the pseudo-perovskite
а	Crystallographic a-axis
b	Crystallographic b-axis
c	Crystallographic c-axis
А	Cationic site occupied by a mono, di, or trivalent large
	cation
В	Cationic site occupied by a tri, penta, or hexavalent small
	cation
A	Alkali metal cation of Dion-Jacobson phase
x+	Formal charge associated with A cation
y+	Formal charge associated with B cation
T <sub>Curie</sub>	Curie temperature
T <sub>melting</sub>	Melting temperature
T <sub>sinter</sub>	Sintering temperature
T <sub>DTG</sub>	Derivative peak temperature
$\Delta T_{relax}$	Degree of relaxation behaviour
$a_0, b_0, c_0$	Orthorhombic lattice parameters
a <sub>T</sub> , c <sub>T</sub>	Tetragonal lattice parameters
$a_m, b_m, c_m$	Monoclinic lattice parameters
V <sub>m</sub>	Monoclinic unit cell volume
Vo	Orthorhombic unit cell volume
δ	Orthorhombicity
$\rho_{\rm XRD}$	Theoretical X-ray density
+q	Positive charge
-q	Negative charge
μ <sub>d</sub>	Dipole moment
1	Finite distance
Е	Electric field
D	Phase of induction
α <sub>m</sub>	Molecular polarisability
x(t)	Time variable displacement
γ	Damping coefficient
W	Potential energy
li,j	Charge transfer rate
r <sub>i,j</sub>	Hopping distance
بح	Localization length
$\Delta_{i,j}$	Transition energy
f	Frequency in Hz
ω	Angular frequency in rad/s
ω <sub>R</sub>	Resonant angular frequency
ε <sub>r(max)</sub>	Maximum for the real part of the complex relative permittivity
	r

ε <sub>r(max)</sub>	Maximum for the imaginary part of the complex relative
( <b>(</b> )	permittivity
e0 *	Permittivity of free space
ε <sub>r</sub>	Complex relative permittivity
ε <sub>r</sub>	constant
ε <sub>r</sub>	Imaginary part of the complex relative permittivity or dielectric loss
$\varepsilon_{r(\infty)}$	High-frequency limit of dielectric constant
$\epsilon'_{r(s)}$	Static value of low-frequency dielectric constant
$\varepsilon_{r(CC)}^{"}$	CC-derived dielectric loss
ε <sub>r</sub> (CD)	CD-derived dielectric loss
ε <sub>r (HN)</sub>	HN-derived dielectric loss
C*	Complex capacitance
Ċ'	Real part of the complex capacitance
с"	Imaginary part of the complex capacitance
C <sub>0</sub>	Capacitance of empty cell
tan δ	Dissipation factor
i	Imaginary operator with $(-1)^{1/2}$
M*	Complex dielectric modulus
м	Real part of the complex dielectric modulus
М"	Imaginary part of the complex dielectric modulus
Z <sup>*</sup>	Complex impedance
z	Real part of the complex impedance
Z"	Imaginary part of the complex impedance
Gp	Parallel conductance
C <sub>p</sub>	Parallel capacitance
R <sub>p</sub>	Parallel resistance
$C_{s}$	Series capacitance
R <sub>s</sub>	Series resistance
R <sub>el</sub>	Electrode resistance
R <sub>sl</sub>	Schottky layer resistance
R <sub>gb</sub>	Grain boundary resistance
R <sub>g</sub>	Grain resistance
C <sub>el</sub>	Electrode capacitance
C <sub>sl</sub>	Schottky layer capacitance
C <sub>gb</sub>	Grain boundary capacitance
Cg	Grain capacitance
$C_{\infty}$	High-frequency limit of capacitance
Ls	Series stray inductance
Q <sub>CPE</sub>	Pre-factor of CPE
$Z_{CPE}$	Impedance of CPE
m	Dispersion index of CPE
$\sigma_{ac}$	Alternating current conductivity

$\sigma_{dc}$	Direct current conductivity
E <sub>a(gg)</sub>	Activation energy for grain growth
E <sub>a(g)</sub>	Activation energy for grain
E <sub>a(gb)</sub>	Activation energy for grain boundary
E <sub>a(el)</sub>	Activation energy for electrode-interface
$E_{a(\sigma_{dc})}$	Activation energy for direct current conductivity
$E_{a(\sigma_{ac})}$	Activation energy for alternating current conductivity
$E_{a(\rho_{dc})}$	Activation energy for direct current specific resistivity
k <sub>B</sub>	Boltzmann constant or constant of proportionality
Ā <sub>D</sub>	Dispersive amplitude of Debye response
$\tau_{\mathrm{D}}$	Relaxation time of Debye response
A <sub>CC</sub>	Dispersive amplitude of CC response
$\tau_{CC}$	Relaxation time of CC response
$\alpha_{\rm CC}$	CC-associated empirical exponent
A <sub>CD</sub>	Dispersive amplitude of CD response
$\tau_{CD}$	Relaxation time of CD response
β <sub>CD</sub>	CD-associated empirical exponent
A <sub>HN</sub>	Dispersive amplitude of HN response
$ au_{ m HN}$	Relaxation time of HN response
$\alpha_{HN}, \beta_{HN}$	HN-associated empirical exponents
V <sub>0</sub>	Doubly ionized oxygen vacancies
h	Electronic holes
e	Excess electrons
$\mathbf{R}^2$	Correlation coefficient of linear fit
Z	Absolute impedance
$\theta_Z$	Impedance phase
R <sub>wp</sub>	Rietveld conceived of weighted profile R-factor
R <sub>exp</sub>	Rietveld conceived of expected R-factor
R <sub>p</sub>	Rietveld conceived of profile R-factor
$\chi^2$	Goodness of fit value, $(R_{wp}/R_{exp})^2$

### **CHAPTER 1**

#### **INTRODUCTION**

### 1.1 Research Background

Dielectrics, their breadth of discipline in general classified into physics, electrical engineering, materials science, and chemistry, are publicly recognized for their passive electrical insulation properties under the influence of magnetic, electric, or electromagnetic field. From a global perspective view yearly, the research output in the dielectric field is in the rapid ascending order, notably in South-East Asia countries which published considerable dielectric studies. As traced back to the early year before 1980, lead and barium-containing perovskite compounds have been the dominant scientific studies in various matter forms (polymer, ceramic, thin film, glass, rubber, liquid, gas) and were being investigated in the dielectric functions of polarization, relaxation, conduction, and high frequency phenomena. As time ages by, approaches have been taken toward driving down the extensive use of lead following its lifetime adverse effects on environment and human health. In particular, this cumulative metal toxicant poses a high exposure risk to the occupational health during the manufacture of lead zirconium titanate (PZT)-based nanotechnologies. Yet the demands of PZT-based high performance nanofabrication in sensors and actuators are dramatically growing since the discovery of pioneering PZT ceramic with exceptional piezoelectric properties by the Japanese physicists in 1952 (Shirane and Suzuki, 1952). In order to comply with the Restriction of Hazardous Substances Directive, lead-free and environment-friendly alternatives are of priority since year 2003 thereof, being the primary on-going quests for at least comparable piezoelectric and ferroelectric attributes to their lead counterparts. Until now, bismuth-based materials have gained the most popularity among the other non-toxic alternatives, being featured with superior properties across many disciplines as a consequence of their unique crystal structures. These types of lighter, synthetic materials are further described in the later section, whose foremost bismuth titanate (Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub>) is meant to act as the parent subject for the present studied variants of related structures.

### 1.2 Understanding of Bismuth-based Aurivillius Ceramics

Bismuth (Bi)-based ceramics are undeniably categorized as one of the complexoxide families of layered structural-type involving the basis of perovskite structure. The prototypical representation of layered Bi-containing oxides is  $Bi_4Ti_3O_{12}$  (n = 3, being the number of oxygen octahedron that forms the pseudo-perovskite blocks), whose crystal structure as shown in Figure 1.2(a) is built by three interleaving pseudo-perovskite blocks  $(Bi_2Ti_3O_{10})^{2^-}$  between fluorite-like  $(Bi_2O_2)^{2^+}$  slabs stacked along a crystallographic c-direction. This sandwiched-like intergrowth configuration is known as Aurivillius phase, named in respect to Bengt Aurivillius who pioneered  $Bi_2O_3$ -TiO<sub>2</sub> solid solution in 1949 (Aurivillius, 1949). A general expression  $(Bi_2O_2)^{2^+}(A_{n-1}B_nO_{3n+1})^{2^-}$  applicable to the exploiting of other homologous Aurivillius series in one crystallographic direction was developed. Here, the notations A and B are the cationic sites occupied by larger (i.e., mono, di, or



chemistry of Aurivillius phase to  $A'[A_{n-1}B_nO_{3n+1}]$  of Dion-Jacobson phase (see Figure 1.4).



Figure 1.2: Aristotype Tetragonal Crystal Structure of Aurivillius Phase (a)  $n = 3 Bi_4Ti_3O_{12}$ , along with Other Orthorhombic-type Aurivillius Phases Characterized by Different Thicknesses of Perovskite-like Slabs as in (b)  $n = 1 Bi_2MoO_6$ , (c)  $n = 4 Bi_5FeTi_3O_{15}$ , and (d)  $n = 6 Bi_7Fe_3Ti_3O_{21}$ 

![](_page_48_Picture_0.jpeg)

![](_page_49_Picture_0.jpeg)

![](_page_50_Picture_0.jpeg)

of a high non-linear dielectric response. The phase transition of  $Bi_4Ti_3O_{12}$  from tetragonal to orthorhombic structure (i.e. changes in the lattice parameters by lowering of symmetry as shown in Figure 1.8) upon cooling undergoes three structural distortions simultaneously as follows (Benedek et al., 2015):

- a) Off-centering of Bi cation and O anion in the perovskite blocks.
- b) Octahedral tilting along the crystallographic a-direction.
- c) Rotation of oxygen octahedra around the crystallographic c-direction.

![](_page_51_Figure_4.jpeg)

Figure 1.7: Curie Temperature T<sub>Curie</sub> Determinations of Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> at Constant Frequency 1 MHz. Note that the Samples were Produced via Self-propagating High-temperature Synthesis (SHS) and Solid State Reaction (Source: Macedo et al., 2004)

![](_page_51_Figure_6.jpeg)

Figure 1.8: Phase Transition of  $Bi_4Ti_3O_{12}$  with the Variation of Lattice Parameters as a Function of Temperature. Orthorhombic-associated Lattice Parameters are Indicated by  $a_0$ ,  $b_0$ , and  $c_0$ ; while Tetragonal-associated Lattice Parameters are Indicated by  $a_T$  and  $c_T$ , Respectively (Source: Jardiel et al., 2008)

#### **1.3 Problem Statement**

Researches on Bi-layered oxides have always been accompanied by a number of shortcomings that tend to limit the leveraging of their key resources, varying according to the fabrication techniques. The expected challenges hereafter consider the solid state synthesis via conventional and high energy milling, both of which are employed in the current research. In the conventional processing, the reaction path takes place in two-steps heat treatment, opening up the possibility of causing the evaporation of bismuth oxide Bi<sub>2</sub>O<sub>3</sub> species at high sintering temperatures due to its hygroscopic nature in Bi volatility. This is the unfavourable situation triggering conceivably the materials of non-stoichiometric form, thus leading to the consequences of having oxygen deficiencies and instability in oxidation state of titanium (Ti) ions in which the positioning and generation are difficult to control (Zhang et al., 2014; Siriprapa et al., 2013). The volatile species provokes further complication on the possible formation of intermediate phases upon sintering process, such as sillenite phase which reacts with the presence of precursor TiO<sub>2</sub> phase toward the synthesis of primary Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> pure phase. Such temperaturedriven transient intermediate phase formation may result in poor densification of the materials associated with exaggerated grain growth, dampening the dielectric properties which immediately raise a question on whether the usage of starting nanopowders herein would manage to provide improved reactivity for the densification of end product during the conventional sintering process.

The above mentioned inefficiencies in the conventional processing are practically preventable through the process of high energy milling. Such milling speed is apparently intense, being advantageous in avoiding the evaporation of Bi<sub>2</sub>O<sub>3</sub> during the subsequent sintering as the volatile Bi ions are effectively relieved at the sites of high-impact ball collision where the mechanochemical reaction takes place in the condition of instant "hot spots" of localized heat and pressure (Friščić et al., 2013). As a result, mechanical energy is transferred into the system, providing mass transfer to achieve a potential direct milling synthesis of single-phase Bi-based material whilst inducing better sinterability for the concomitant formation of amorphous and crystalline phases. In some particular cases such as the pure and erbium (Er)-doped Bi<sub>5</sub>CrTi<sub>3</sub>O<sub>15</sub>, the direct synthesis difficulties by intensive milling alone can be anticipated from the viewpoint of multi-valence configuration of chromium (Cr) cation and the strength of Er-cation substitution, thus the corresponding complete phase formations require sintering. Also these present a major concern in which the process ahead may stand a chance to leave behind a powder contamination to the end product. One of the many sources of contamination can be intuitively attributed to the adsorption of oxygen and nitrogen on the powder and mill media surfaces especially under the ambient atmosphere (Suryanarayana, 2004b), creating impurity problems that definitely constrain the study to some extent.

On dielectric data analysis, the interpretations of the variation of real and imaginary components of the complex permittivity have been a challenging goal in both theoretical and practical significances, especially under frequency domain response. The experimental dielectric data upon simulation require theoretical support to extract more detailed information about the polarization phenomena. On this matter, an analytical dielectric function based on any superposition of the Debye, Cole-Cole, Cole-Davison, and Havriliak-Negami dispersion mechanisms plus a direct current conductivity term is taken into consideration (Grosse, 2014), which is useful to approximate the dispersion behaviour. As this fitting process is totally based on trial and error approach, figuring out the appropriate initial guess values for each parameter with sufficient accuracy becomes time consuming, being particularly challenging in Bi-based materials due to the anisotropy of properties on dielectric relaxation.

The origin of dielectric properties associated with these materials is always related to the oxygen vacancies, which raise a question of the ways the defects, or more specifically the missing oxygen atoms do the trick and to what degree they contribute to ion transport at the stage of different sintering temperatures in different processing methods. The challenge continues as to answer on how the emergence of rare-earth Er element as A-site substitute in influencing the dielectric properties of threelayered Bi<sub>4</sub>Ti<sub>3</sub>O<sub>12</sub> and four-layered Bi<sub>5</sub>CrTi<sub>3</sub>O<sub>15</sub> compounds, also, to what extent these modified materials might function when subjected to different sintering temperatures and processing methods. Since the best fits of each dielectric data follow algorithm that indeed is purely mathematical derived, it turns out to be an arduous task to shed light on the underlying physical nature governing the relaxation polarization. Therefore, other empirical dielectric functions such as the representations in terms of dielectric modulus, conductivity, and impedance are proposed, which are expected to convey the supportive physical processes from their perspectives.

#### 1.4 Scope of Research

In this research, solid state reaction via conventional and high energy milling methods are employed to synthesize  $n = 3 Bi_4Ti_3O_{12}$  and higher homologous Aurivillius oxides  $n = 4 Bi_5CrTi_3O_{15}$  at various sintering temperatures ranging from 700°C to 1000°C. Following the same procedures, the base  $Bi_4Ti_3O_{12}$  and  $Bi_5CrTi_3O_{15}$  compounds are tuned by substituting single isovalent  $Er^{3+}$  cation composition on the Bi-sites of the structure, forming the modified  $Bi_{3.25}Er_{0.75}Ti_3O_{12}$  compound and turning out to be the first time in synthesizing  $Bi_{4.25}Er_{0.75}CrTi_3O_{15}$  compound. These series altogether are systematically made in attempting to answer the following utmost objectives:

- 1) To identify the role of Bi-site substitutional  $Er^{3+}$  cation and to make a comparison of methods between similar samples in view of the phase formation, microstructure, and dielectric properties.
- 2) To determine the underlying physical interpretations of the dielectric properties in the samples through an empirical fit of relaxation functions in the frequency range of 100 Hz 10 MHz at room temperature and elevated temperatures in the range of  $100 300^{\circ}$ C.
- 3) To study the effect of sintering temperature on densification and microstructure that controls the dielectric properties of the samples.

### **1.5** Dissertation Organization

The dissertation is organized into five chapters. Up to this point we have built a better understanding of how the Bi-related Aurivillius ceramics behave and perform mostly in terms of crystallographic aspect. This is followed by the consideration of potential issues behind the synthesis and characterization. In addition, the present research directions and strategies are also clearly defined.

We continue in Chapter 2 with a specific review of the literatures concerning the synthesis of  $Bi_4Ti_3O_{12}$  and its higher homologous derivatives, starting with the attempt to gather relevant scientific information limited to the published literatures on the solid state syntheses using conventional and high energy milling approaches. Following this manner, the subsequent discussion in the aspects of electrical and structural studies is developed, focusing on a wide range of past achievements relating to the parent and their modified Aurivillius compounds. The last discussion in this chapter is devoted to the practical significance of frequency domain in interpreting particularly the dielectric phenomena, and at this stage, to enter into the dielectric concept at the most fundamental level, as well as an outline of some aspects of presentation of dielectric data.

Chapter 3 provides a descriptive procedure of the synthesis techniques employed, detailing every process involved which begins with the sample preparation and ends with the methods of characterization and measurement. Chapter 4 presents a wide range of experimental findings. We begin with the interpretations of each system from thermal, crystallographic, and morphological analyses, all of which are made clearer independently according to the type of processing methods concerned. While presenting the room-temperature measured dielectric data involving the manipulated variable of frequency, the treatment of interpretational analysis based on an empirical fitting function is provided. In the same way, some significances of frequency domain dielectric response measured over a range of temperatures are highlighted. In order to make the fullest possible understanding of the frequency range of room-temperature measured dielectric data, impedance representations of these data are presented along with an equivalent circuit modelling. A comparison of processing methods evaluated from the aspect of dielectric analysis is also given. Chapter 5 concludes the main findings and suggests the prospect of future work.

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